

# GDU 90 20302

## **GATE DRIVE UNIT**

This data sheet should be used in conjuction with the publication entitled GDU9X-XXXXX Series, Gate Drive Unit.

APPLICATIONS KEY PARAMETERS

■ Used with Gate Turn-Off Thyristors in high current switching applications

 $\begin{array}{ll} I_{\text{FGM}} & 40\text{A} \\ I_{\text{G(ON)}} & 8\text{A} \\ \text{d}I_{\text{GQ}}/\text{dt} & 40\text{A}/\mu\text{s} \end{array}$ 

### **CONDITIONS - (UNLESS STATED OTHERWISE)**

| V <sub>1</sub> = +5V                          | V <sub>2</sub> = +15V |                                    | V <sub>3</sub> = -15V |  |  |
|---|-----------------------|------------------------------------|-----------------------|--|--|
| Test circuit GTO                              |                       | DG758BX                            |                       |  |  |
| GDU connection to GTO                         |                       | 500mm CO - AX cable type RC5327230 |                       |  |  |
| Test circuit emitter and gate drive emitter   |                       | Honeywell sweetspot HFE 4020 - 013 |                       |  |  |
| Test circuit emitter current                  |                       | 30mA                               |                       |  |  |
| Test circuit receiver and gate drive receiver |                       | Honeywell sweetspot HFD 3029 - 002 |                       |  |  |

#### **ELECTRICAL CHARACTERISTICS**

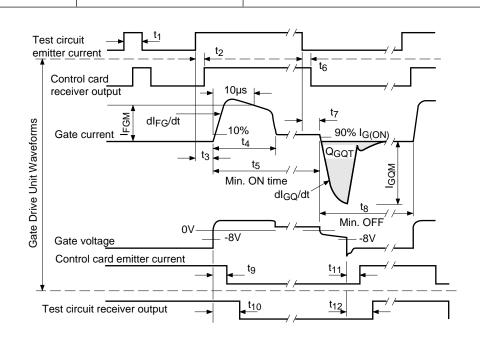
| Symbol               | Parameter                             | Conditions  | Min. | Тур. | Max. | Units |
|----------------------|---------------------------------------|---|------|------|------|-------|
| I <sub>V1</sub>      | +5V PSU current                       | 500Hz, 50% duty cycle   | -    | -    | 4.40 | А     |
| I <sub>V2</sub>      | +15V PSU current                      | 500Hz   | -    | -    | 0.48 | Α     |
| I <sub>V3</sub>      | -15V PSU current                      | 500Hz, I <sub>T</sub> = 3000A<br>GTO T <sub>j</sub> = 125°C           | -    | -    | 10.0 | Α     |
| V <sub>1(Min)</sub>  | +5V PSU minimum                       | -   | 3.8  | -    | -    | V     |
| V <sub>2(Min)</sub>  | +15V PSU minimum                      | -   | 14.0 | -    | -    | V     |
| V <sub>3(Min)</sub>  | -15V PSU minimum                      | -   | 14.0 | -    | -    | V     |
| I <sub>FGM</sub>     | Peak forward gate current             | -   | 40   | -    | -    | А     |
| I <sub>G(ON)</sub>   | On-state gate current                 | -   | -    | 8    | -    | А     |
| dl <sub>FG</sub> /dt | Rate of rise of positive gate current | Measured 10 - 75% I <sub>FGM</sub>                                    | -    | 40   | -    | A/μs  |
| dl <sub>GQ</sub> /dt | Rate of rise of negative gate current | I <sub>T</sub> = 3000A, 90% I <sub>G(ON)</sub> - 50% I <sub>GQM</sub> | -    | 40   | -    | A/μs  |

### **TIMING CHARACTERISTICS**

| Symbol            | Parameter Conditions   |                                  | Min. | Тур.             | Max. | Units |
|-------------------|--|----------------------------------|------|------------------|------|-------|
| t,*†              | No response pulse width of input signal  | Adjustable by R81 + R82          | 2    | -                | 3    | μs    |
| t <sub>2</sub>    | Delay time emitter current to receiver o/p   | р -                              |      | -                | 0.8  | μs    |
| t <sub>3</sub> *† | Turn-on delay emitter current to 10% I <sub>FGM</sub>                                |                                  | 5.2  | -                | 6.2  | μs    |
| t <sub>4</sub>    | I <sub>FGM</sub> pulse width   | -                                | -    | 16               | -    | μs    |
| t <sub>5</sub> *  | Minimum on time<br>10% I <sub>FGM</sub> to 90% I <sub>G(ON)</sub>                    | Adjustable by R37                |      | -                | 110  | μs    |
| t <sub>6</sub>    | Receiver storage time  | -                                |      | -                | 0.9  | μѕ    |
| t <sub>7</sub>    | Turn-off delay. Emitter current to 90% I <sub>G(ON)</sub>                            |                                  | 1.5  | -                | 2.3  | μs    |
| t <sub>8</sub> *  | Minimum off time<br>90% I <sub>G(ON)</sub> to 10% I <sub>FGM</sub> Adjustable by R38 |                                  | 80   | -                | 110  | μs    |
| t <sub>9</sub>    | Delay time<br>Gate volts to o/p emitter current                                      | -                                | -    | 0.1              | -    | μs    |
| t <sub>10</sub>   | Turn-off delay<br>Gate volts to test receiver o/p                                    | -                                | -    | 0.7              | -    | μs    |
| t <sub>11</sub>   | Storage time<br>Gate volts to o/p emitter current                                    | Measured at low I <sub>GQM</sub> | -    | 0.1 <sup>1</sup> | -    | μs    |
| t <sub>12</sub>   | Turn-on delay Gate volts to test receiver o/p  | Measured at low I <sub>GQM</sub> | -    | 0.8¹             | -    | μs    |

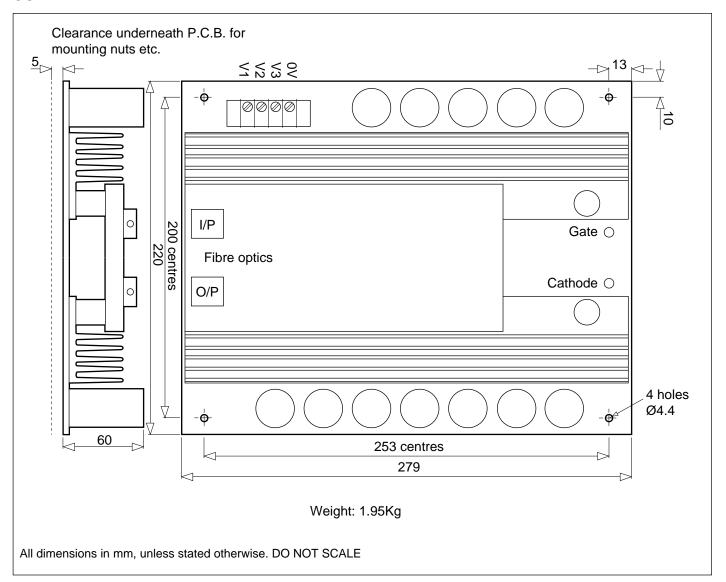
<sup>\*</sup>  $t_1$ , $t_3$ , $t_5$ , $t_8$  are factory settings.

<sup>1.</sup> Varies with  $I_{\text{GQM}}$  due to gate lead impdeance.



<sup>&</sup>lt;sup>†</sup> Adjustment of t<sub>1</sub> alters t<sub>3</sub>.

### **OUTLINE**





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